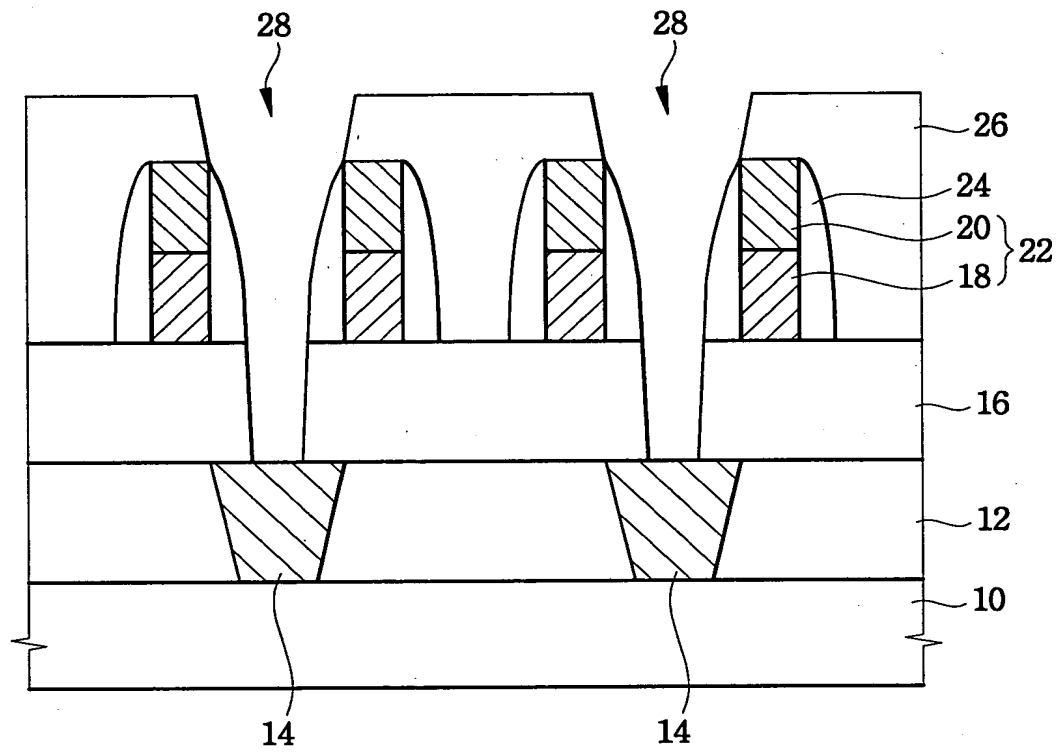


[illegible]

This cross-sectional view shows a substrate 10 with a trench 12. A gate stack 14 is formed in the trench, and a gate electrode 16 is formed on top of the gate stack. The gate stack 14 is composed of a gate oxide layer 18 and a gate electrode layer 20. The gate electrode layer 20 is also formed on the top surface of the substrate 10, forming a gate electrode 24. The gate oxide layer 18 is also formed on the top surface of the substrate 10, forming a gate oxide layer 22. The gate oxide layer 22 is also formed on the top surface of the substrate 10, forming a gate oxide layer 24.

FIG. 1C
(PRIOR ART)



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FIG. 2A

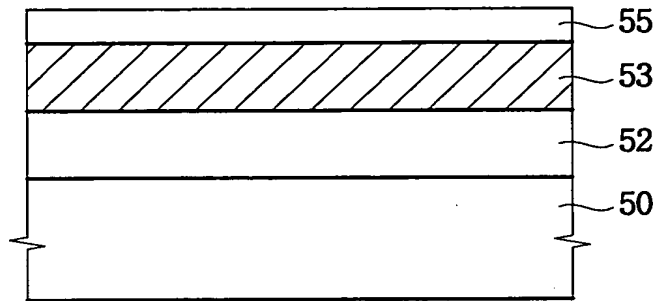


FIG. 2B

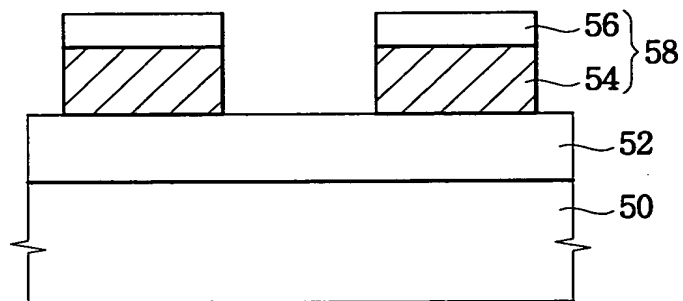


FIG. 2C

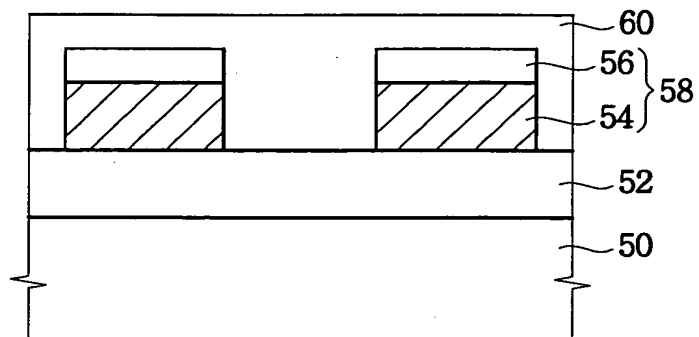
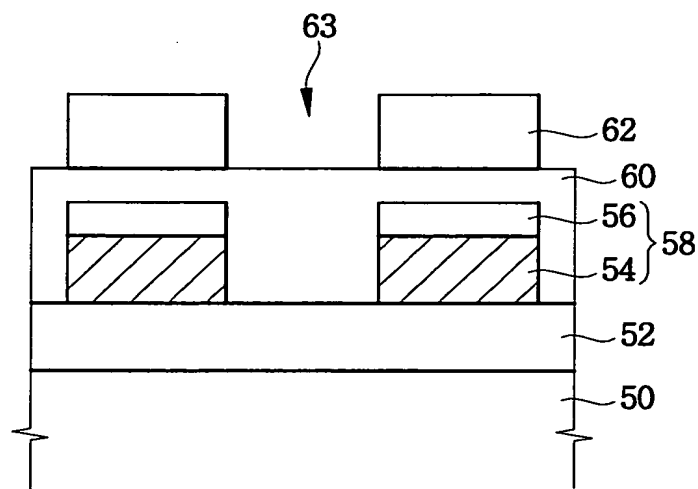


FIG. 2D



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FIG. 2E

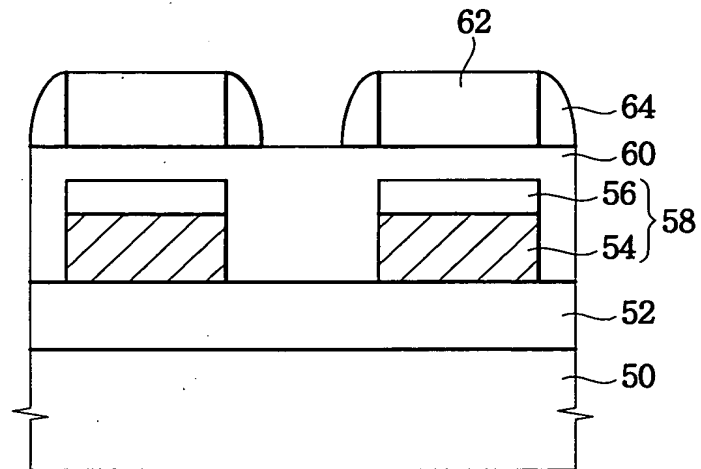
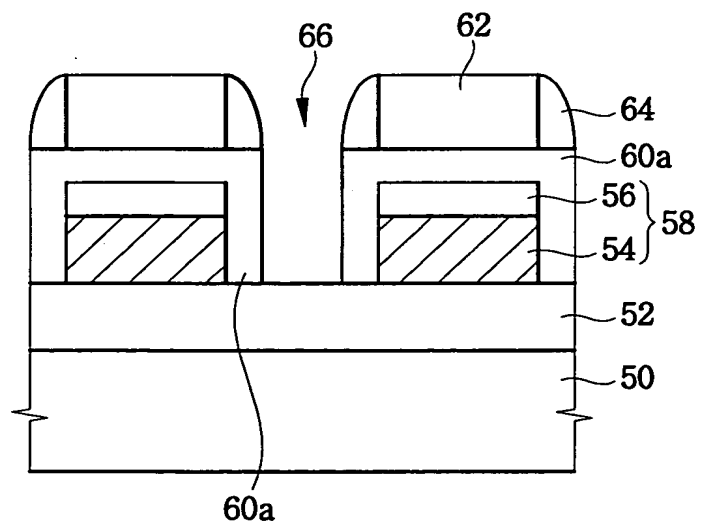


FIG. 2F



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FIG. 3A

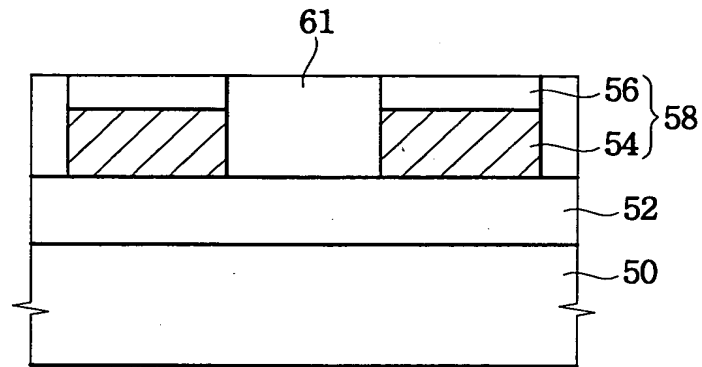


FIG. 3B

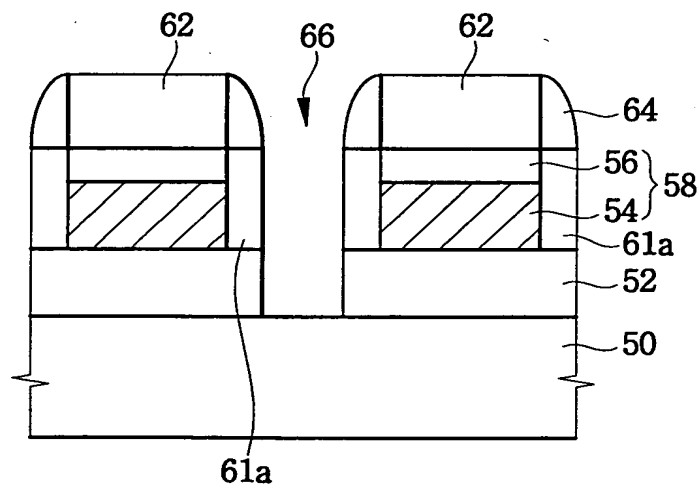


FIG. 4

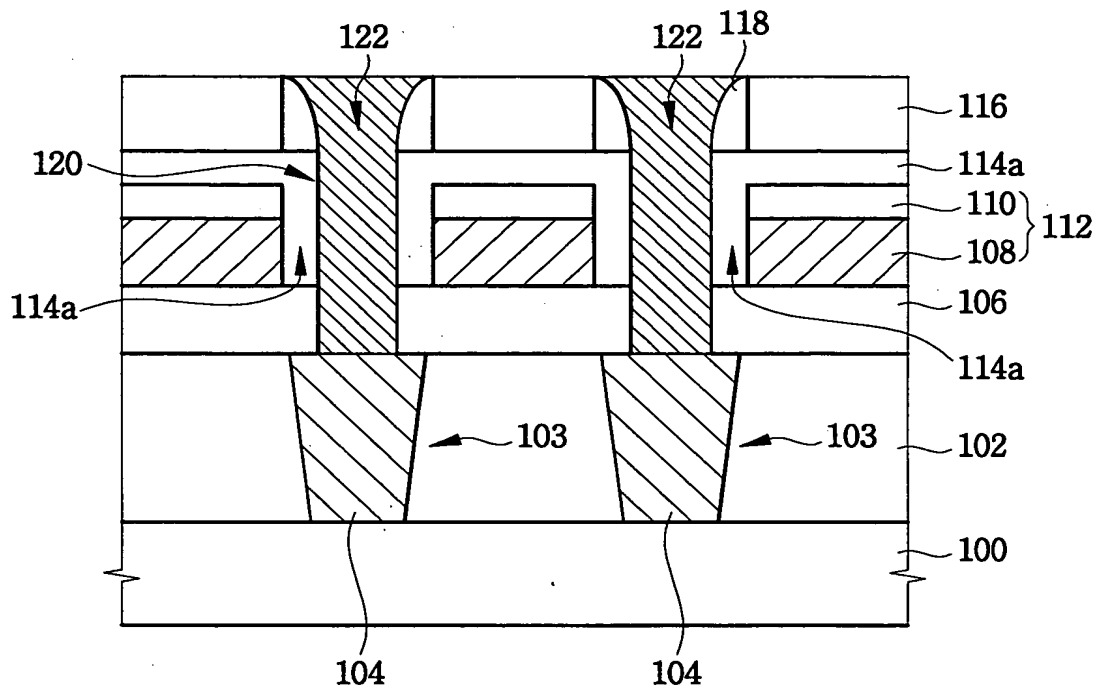


FIG. 5A

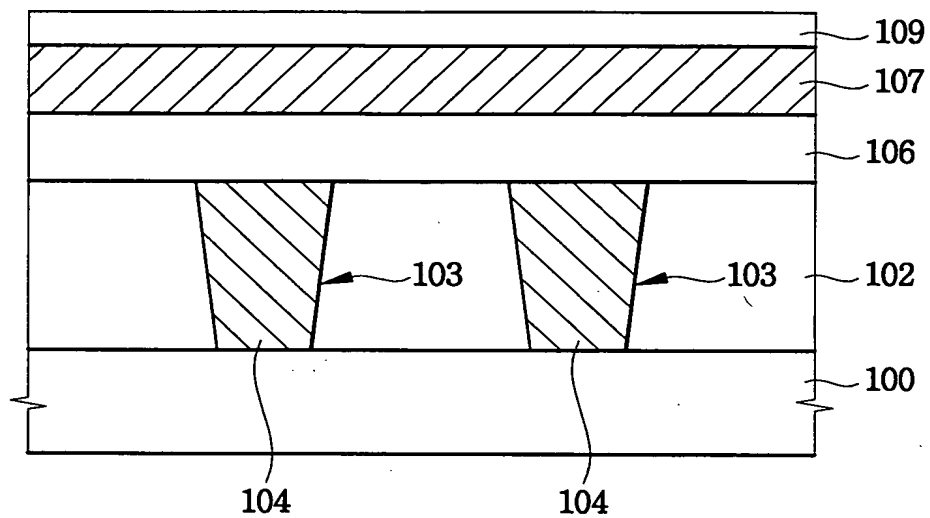


FIG. 5B

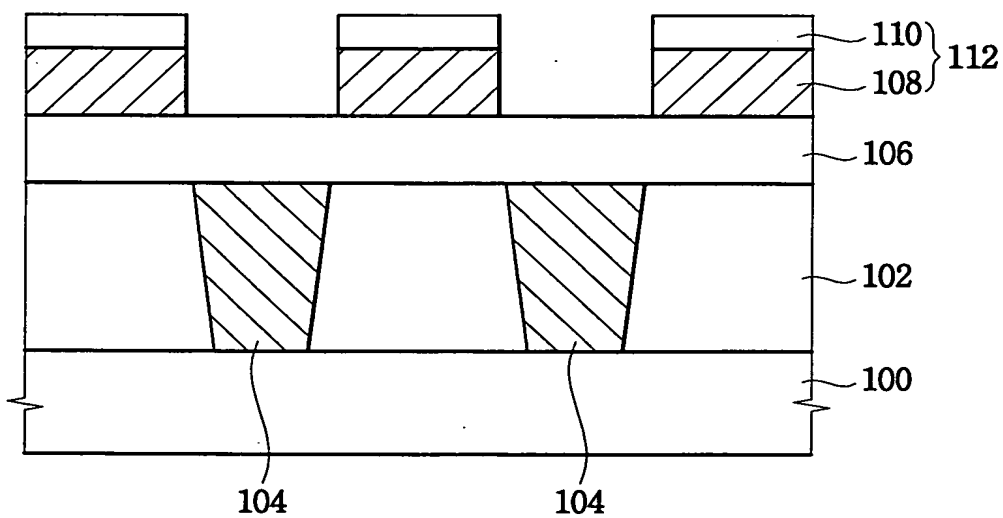


FIG. 5C

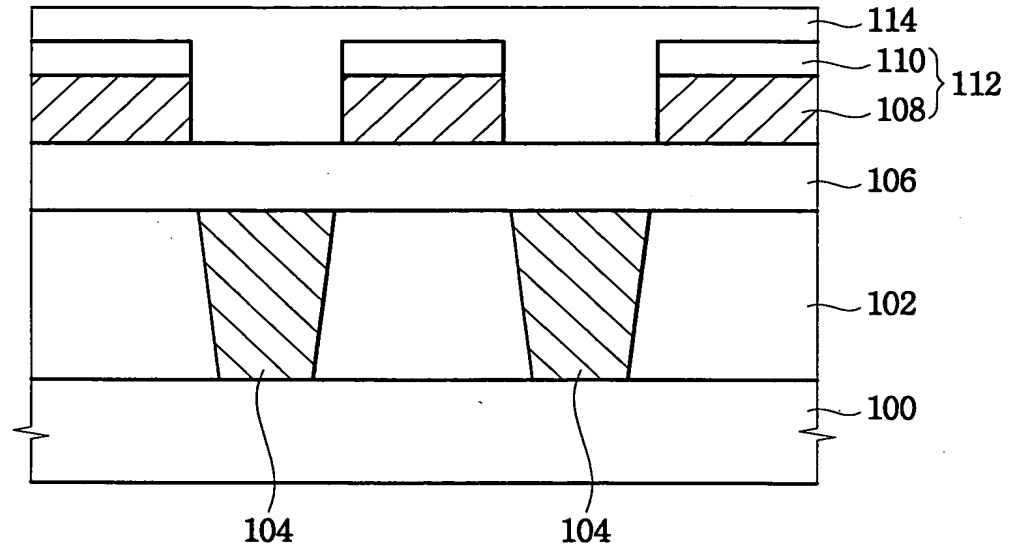
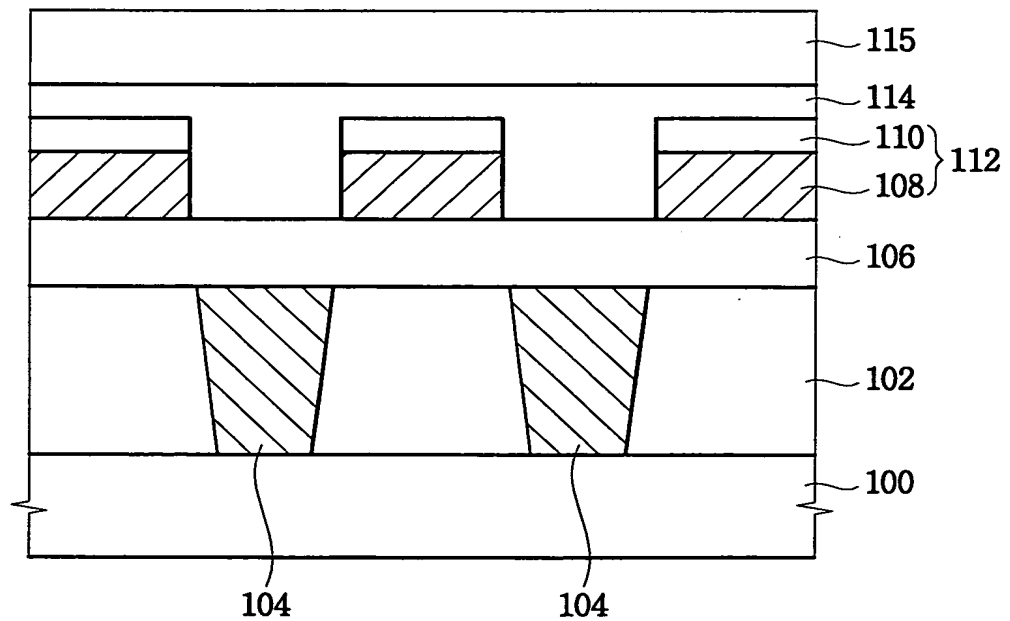


FIG. 5D



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FIG. 5E

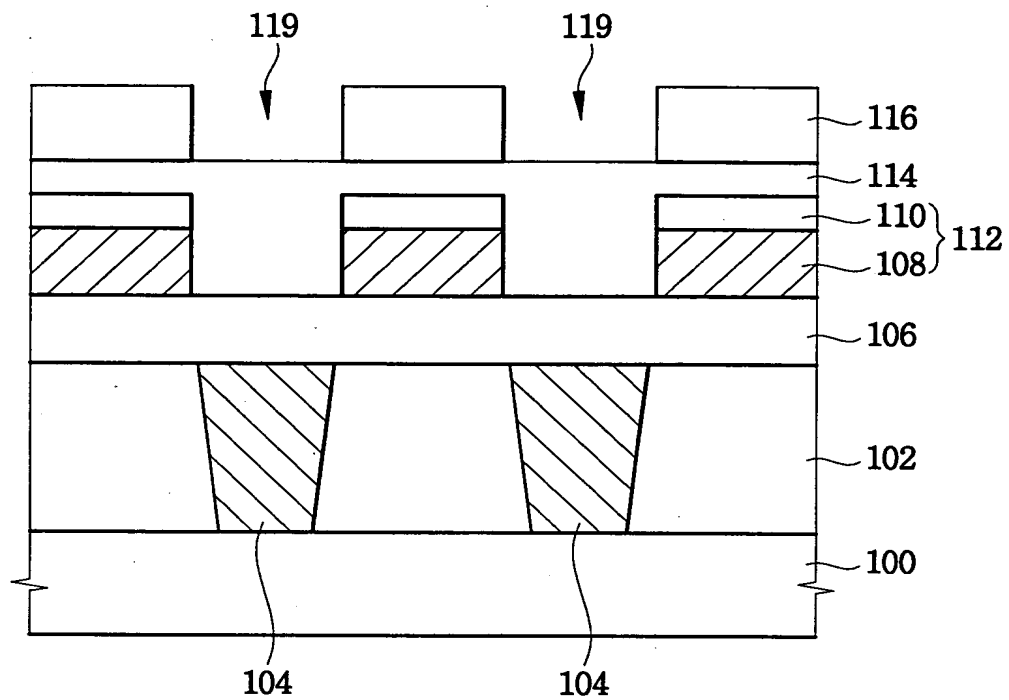
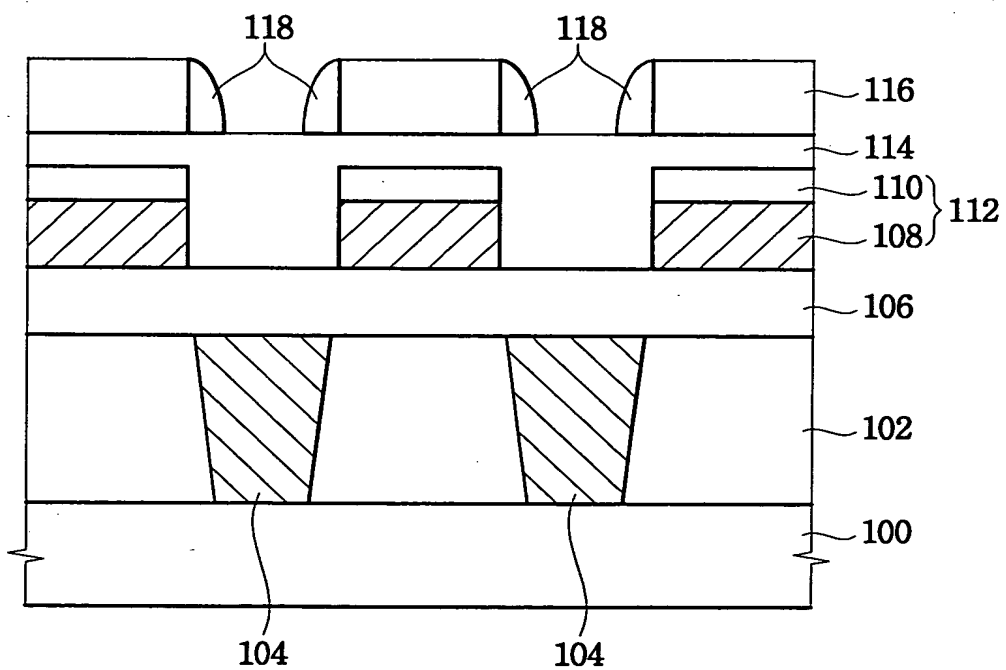


FIG. 5F



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FIG. 5G

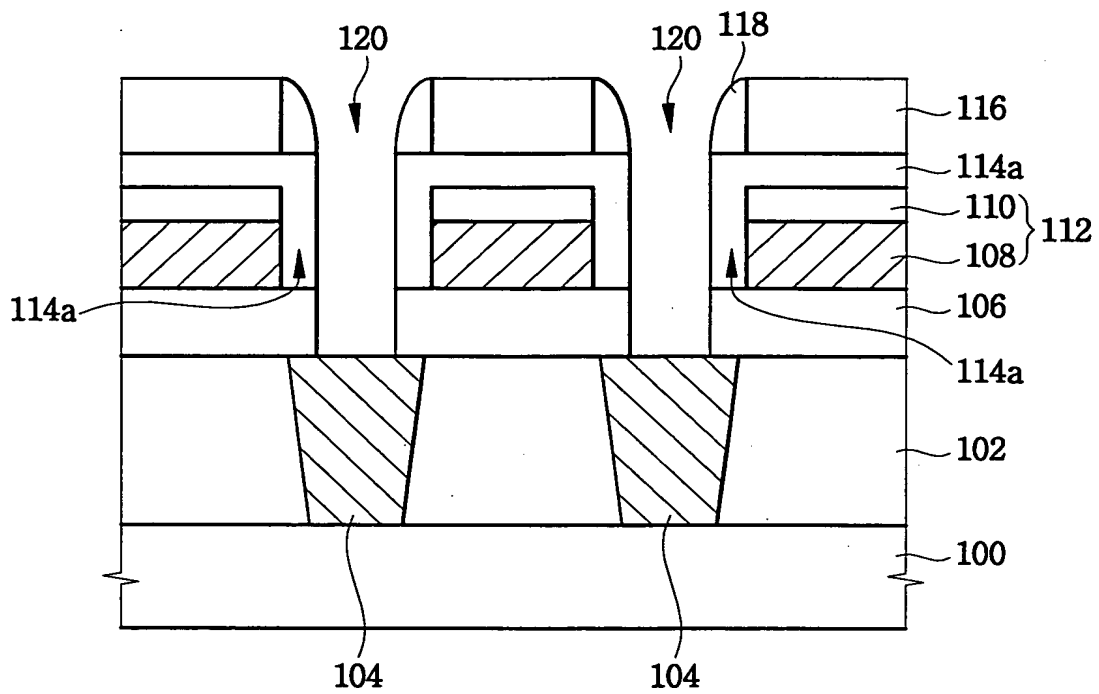
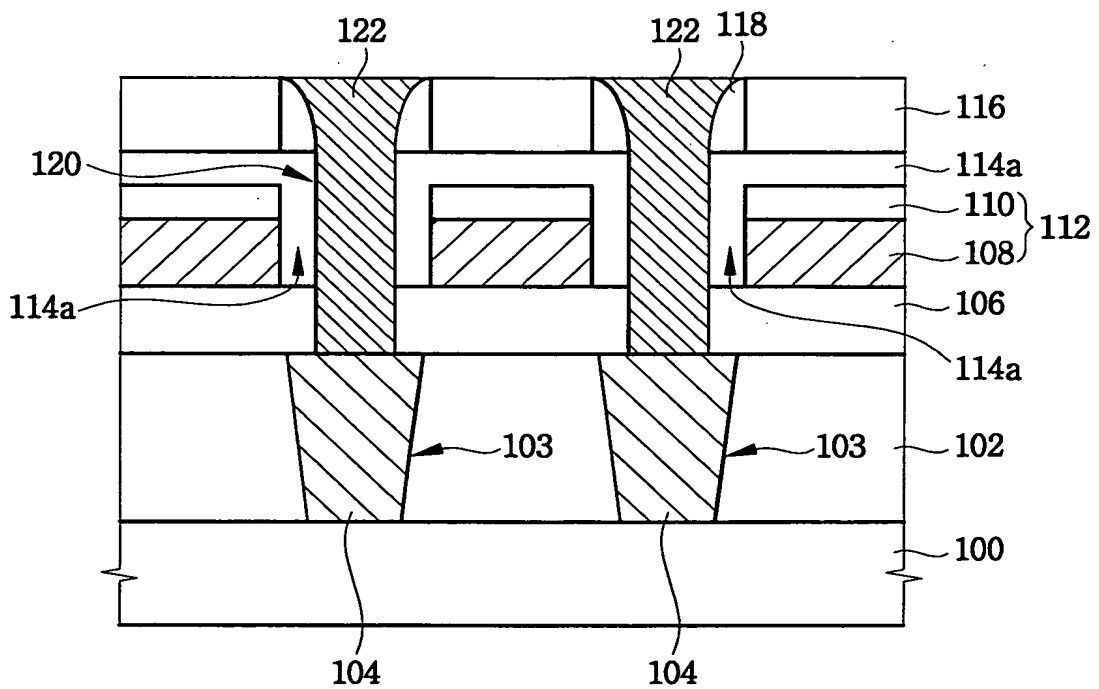


FIG. 5H



[illegible]

